

COL216

Computer Architecture

Input/Output – 5
Secondary Storage
28th March 2022

Hard Disk Drive Example

Capacity: 14TB

Size: 3.5"

RPM: 7200

Data rate: 250 MB/s

Disks: 8 (16 heads)

Sector: 512B (logical)

4096B (physical)

Density: 2426 Kb/in

436 Ktracks/in

Cache: 256 MB

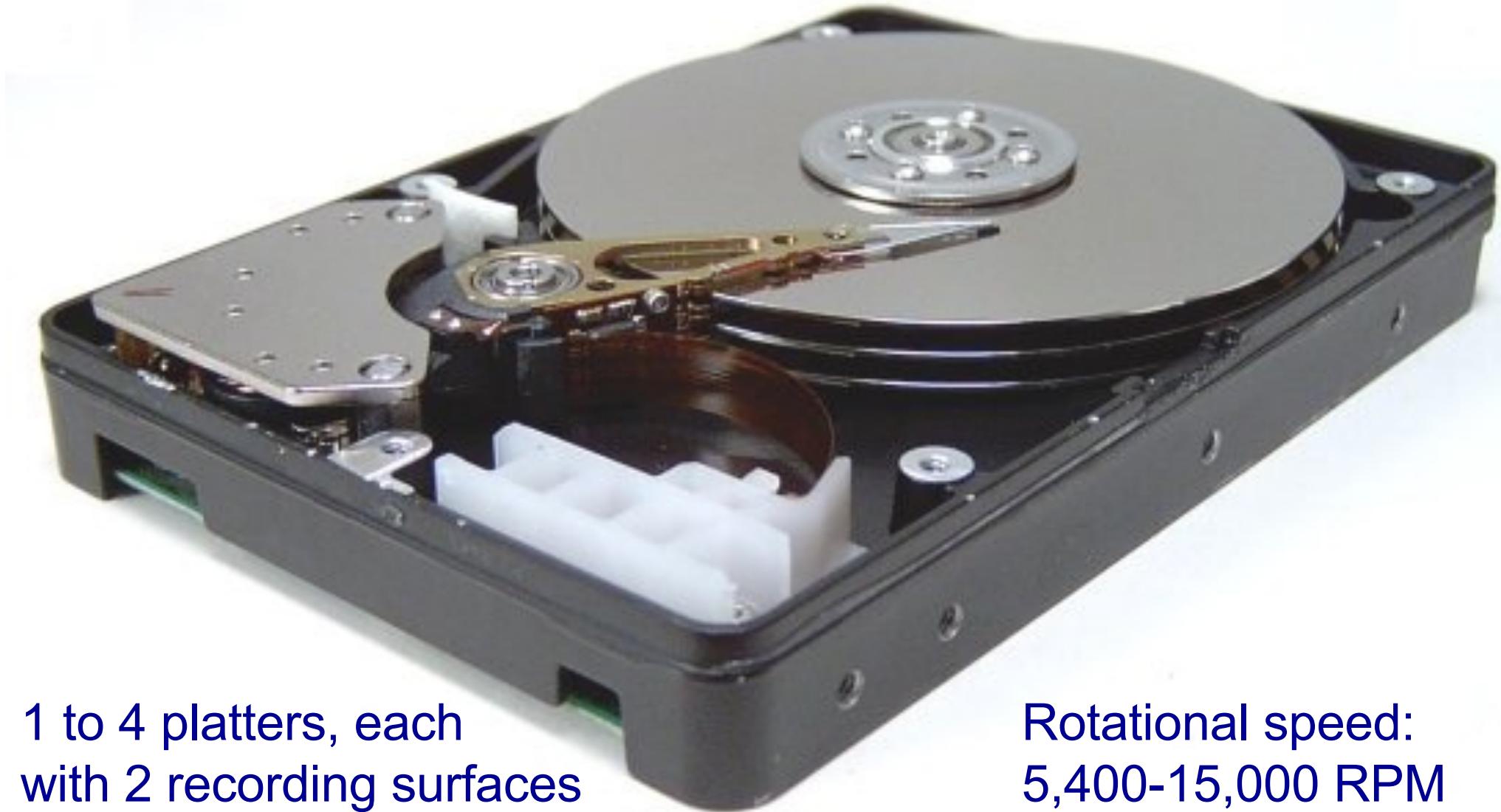


HDD comparison – then and now

Parameter	1957	2018-20	Improvement
Capacity	3.75 MB	18 TB	4.8×10^6
Volume	1.9 m ³	34 cm ³	5.6×10^4
Weight	910 kg	62 g	1.5×10^4
Access Time	600 ms	2.5 – 10 ms	2×10^2
Price	USD 9.2 / KB	USD 24 / TB	3×10^6
Density	2K b / in ²	1.3 TB / in ²	6.5×10^8
MTBF	2000 hrs	285 yrs	1.25×10^3

Source: Wikipedia

Hard Disk Drive



1 to 4 platters, each
with 2 recording surfaces

Rotational speed:
5,400-15,000 RPM

Hard disk drive close-up



Tracks:
10-50 K
Sector/track
100-500
Bytes/sector
512
Seek time:

- Track to track
.5-2 ms
- Average
~10 ms

Disk Latency

Disk Latency =

Seek time + Rotational Latency + data
transfer time + controller overhead

Average rotational latency =

time for $\frac{1}{2}$ rotation =

$(.5 \times 60 \times 1000 / \text{rpm}) \text{ msec}$

Transfer rate = $10^1 - 10^2 \text{ MB/sec}$

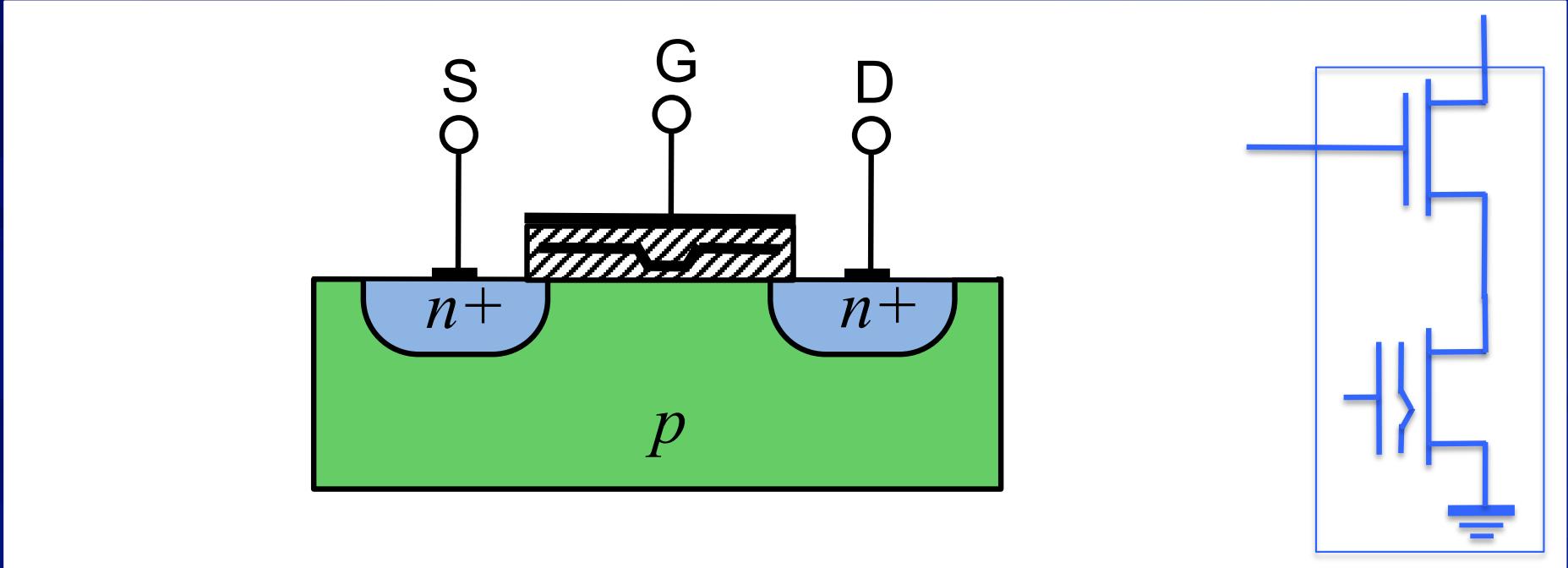
Bulk storage without moving parts

- Flash: semiconductor memory like SRAM, DRAM, but non-volatile like magnetic disks
- Latency is 100–1000 times less than disk
- Smaller, lighter, more power efficient, and more shock resistant than disk
- Has caught up with HDD in capacity, but more expensive
- SSD wears out faster than HDD

Flash Memory

- Semiconductor memory made up of “Floating gate” transistors – these store information in a non-volatile manner
- Reading is fast, but writing is slow as it requires large current
- Writing involves one way state change (e.g. 0 to 1), therefore needs erasing first (make all bits 0 first)
- Block erase, unlike byte erase of EEPROM

Floating gate transistor



Programming: pass high current through channel
Electrons are trapped on the floating gate

Before trapping: like a normal NMOS transistor
After trapping: transistor remains OFF

NOR and NAND flash

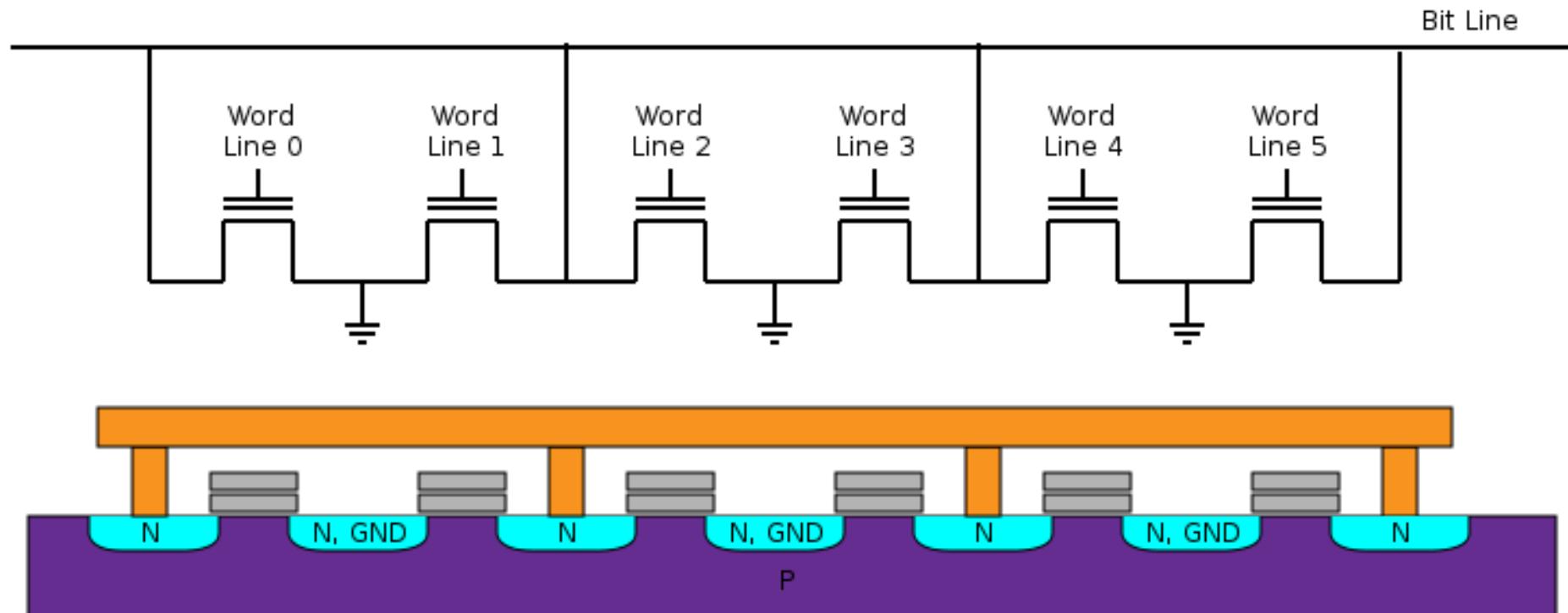
NOR flash

- Structure like NOR gate
- Random access
- Lower density
- More expensive
- Used for BIOS memory

NAND flash

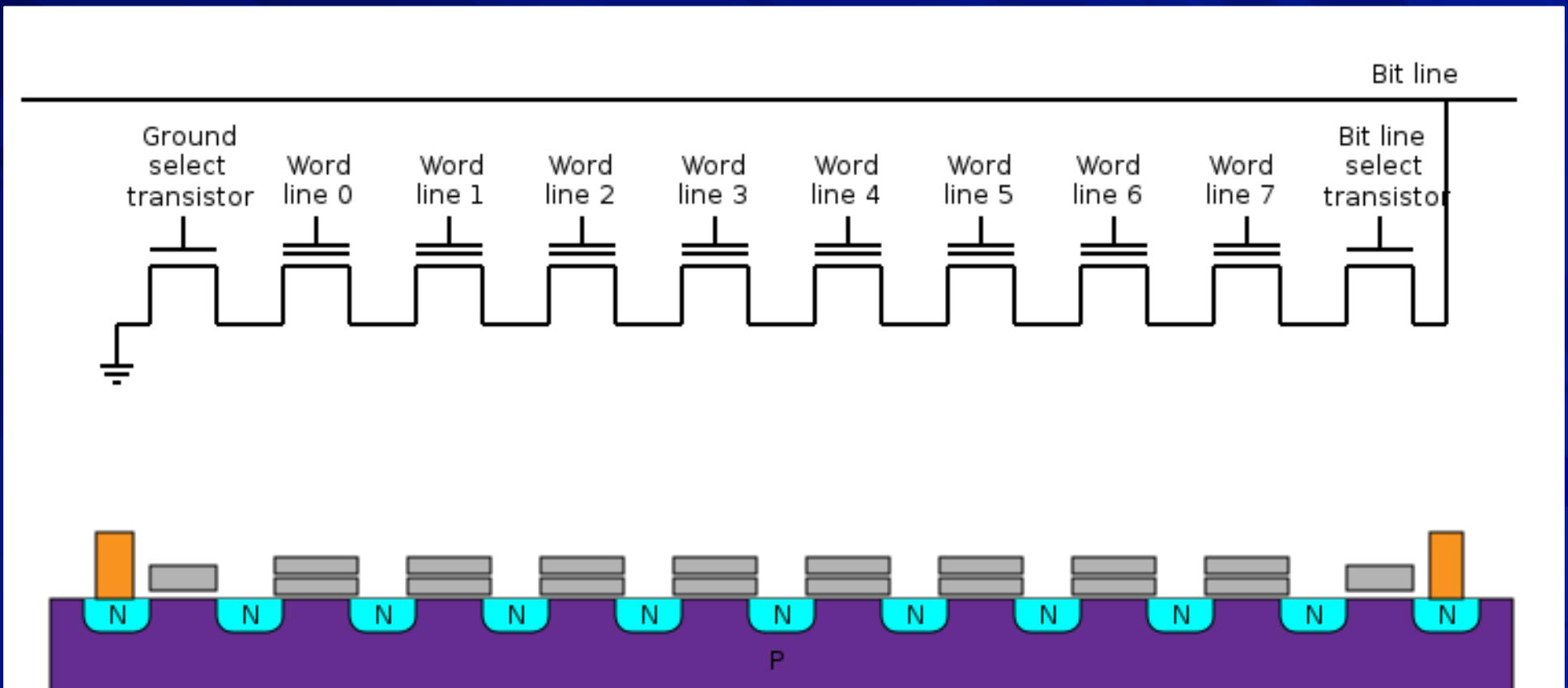
- Structure like NAND gate
- Random plus sequential access
- Higher density
- Less expensive
- Used for pen drive, SD card, SSD
- 32 Mb on BASYS 3

NOR Flash



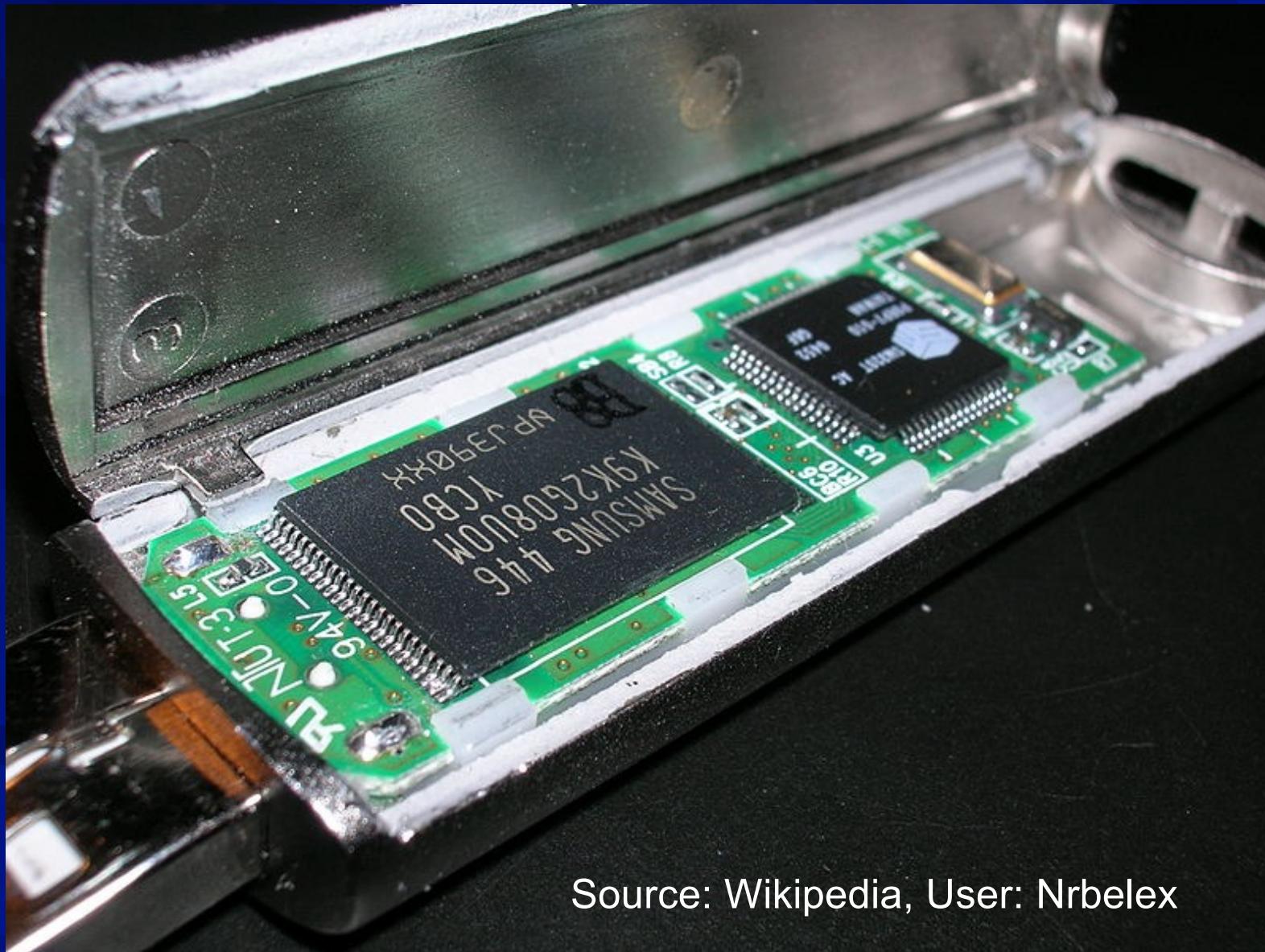
Source: Wikipedia, Author: Cyferz

NAND Flash



Source: Wikipedia, Author: Cyferz

A USB Flash Drive



Source: Wikipedia, User: Nrbelex